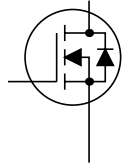
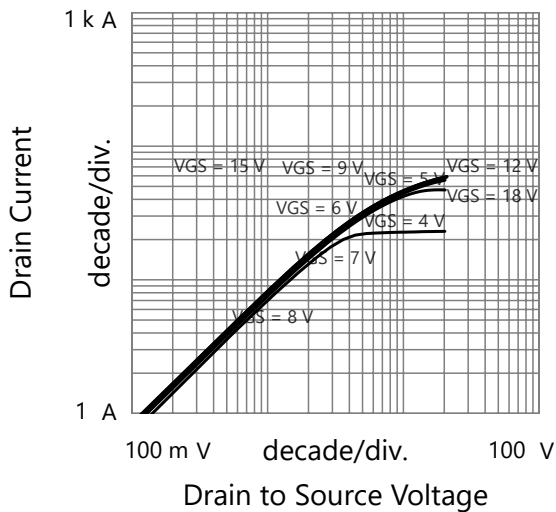


Part Number: 5.IRFP260NPBF
Sample ID: 5B-1
Description: sample
Operator: YM
Measurement Instrument: B1506AH51_MY59200135

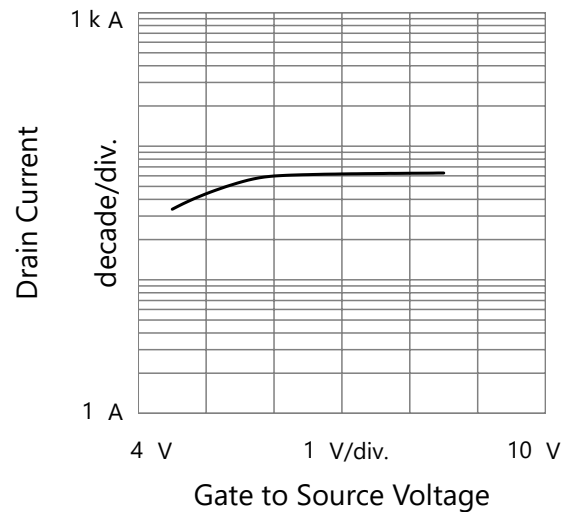


| | | Maximum Ratings | | | | | | |
|---------------|--|--|--|--------------|-------------|-------------|-------------|---------------|
| Symbol | Parameter | Test Conditions | | Value | Unit | Note | | |
| VDSS | Drain to Source Voltage | Tj=-55 °C to 175 °C | | 200 | V | | | |
| VGSS | Gate to Source Voltage | Conitnuous | | -20 to 20 | V | | | |
| IDM | Pulsed Drain Current | Tc=25 °C | | 200 | A | | | |
| ISM | Pulsed Body Diode Current | Tc=25 °C | | 200 | A | | | |
| | | Characteristics Parameters | | | | | | |
| Symbol | Parameter | Test Conditions | | Min. | Act. | Max. | Unit | Note |
| BVDSS | Drain to Source Breakdown Voltage | VGS=0 V, ID=250 μA | | 200 | 228 | | V | |
| IDSS | Drain Leakage Current | VDS=200 V, VGS=0 V | | | 572 p | 25 μ | A | |
| IGSS | Gate Leakage Current | VGS=20 V, VDS=0 V | | | 15.9 p | 100 n | A | |
| IGSS(-) | Gate Leakage Current (-) | VGS=-20 V, VDS=0 V | | -100 n | -17.3 p | | A | |
| VGS(th) | Gate to Source Threshold Voltage (VDS=VGS) | ID=250 μA | | 2 | 2 | 4 | V | |
| RDS(on) | Drain to Source On Resistance | VGS=10 V, ID=28 A, PulseWidth=200 μs | | | 152 m | 40 m | ohm | |
| VSD | Body Diode Forward Voltage | VGS=0 V, IS=28 A, PulseWidth=200 μs | | | 935 m | 1.3 | V | |
| Rg | Gate Resistance | VGS=0 V, f=1 MHz | | | NaN | | ohm | Not specified |
| Ciss | Input Capacitance | VGS=0 V, VDS=25 V, f=100 kHz | | | 957 p | | F | Typ. 4057 pF |
| Coss | Output Capacitance | VGS=0 V, VDS=25 V, f=100 kHz | | | 169 p | | F | Typ. 603 pF |
| Crss | Reverse Transfer Capacitance | VGS=0 V, VDS=25 V, f=100 kHz | | | 31 p | | F | Typ. 161pF |
| Qg | Total Gate Charge | Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A | | | 28.8 n | 234 n | C | |
| Qgs | Gate to Source Charge | Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A | | | 3.55 n | 38 n | C | |
| Qgd | Gate to Drain Charge | Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A | | | 11.3 n | 110 n | C | |

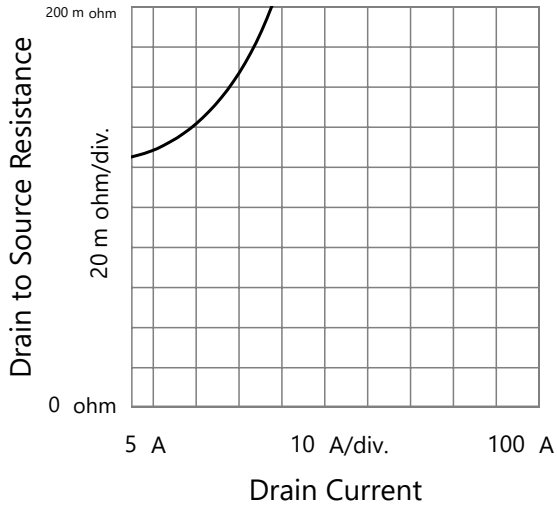
Output Characteristics



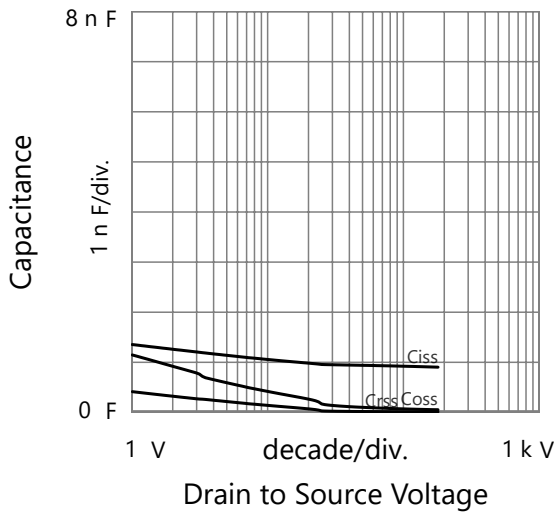
Transfer Characteristics



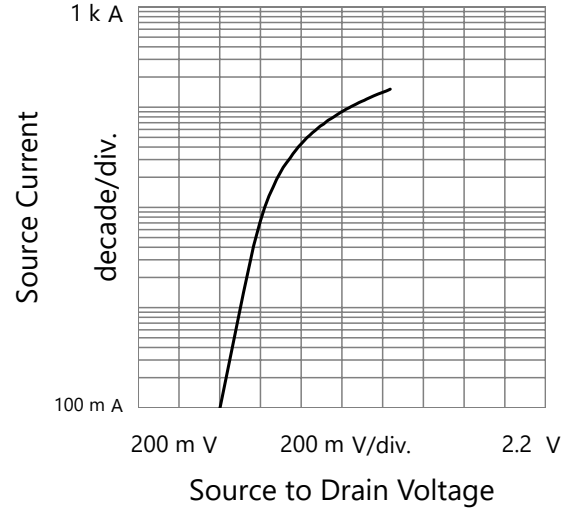
Drain to Source Resistance vs. Drain Current



Capacitances



Body Diode Forward Characteristics



Gate Charge (V_{ds}:160V, I_d:28A)

